OptiMOS®2 Small-Signal-Transistor

Features

- N-channel
- Enhancement mode
- Super Logic level (2.5V rated)
- Avalanche rated
- Footprint compatible to SOT23
- d*v*/d*t* rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101

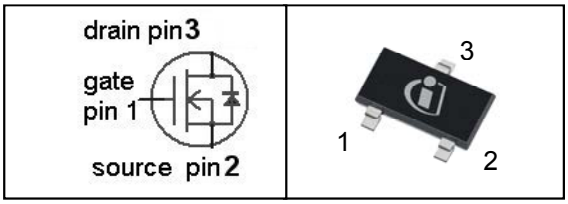
AEC Qualified

RoHS

Product Summary

V_{DS}		20	V
$R_{DS(on),max}$	V_{GS}=4.5 V	21	mΩ
	V_{GS}=2.5 V	33	
I_D		3.8	A

PG-SC-59



Type	Package	Tape and Reel Information	Marking	Lead Free	Packing
BSR202N	PG-SC-59	L6327 = 3000 pcs. / reel	LAs	Yes	Non dry

Maximum ratings, at T_j=25 °C, unless otherwise specified

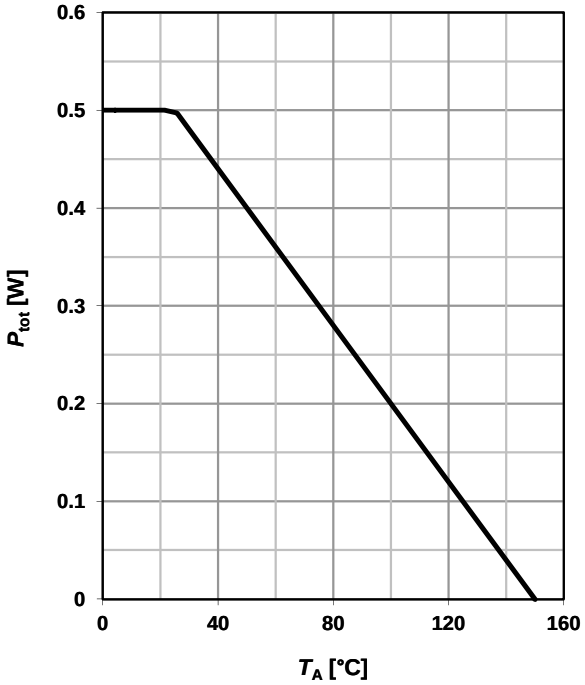
Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	3.8	A
		T_A=70 °C	3.1	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	15.2	
Avalanche energy, single pulse	E_{AS}	I_D=3.8 A, R_{GS}=25 Ω	30	mJ
Reverse diode d*v*/d*t*	d*v*/d*t*	I_D=3.8 A, V_{DS}=16 V, d*i*/d*t*=200 A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±12	V
Power dissipation	P_{tot}	T_A=25 °C	0.5	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
ESD Class		JESD22-A114-HBM	0 (0V to 250V)	
Soldering Temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - minimal footprint	R_{thJA}		-	-	250	K/W
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}= 0 V, I_D= 250 µA	20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=30 µA	0.7	0.95	1.2	
Drain-source leakage current	I_{DSS}	V_{DS}=20 V, V_{GS}=0 V, T_j=25 °C	-	-	1	µA
		V_{DS}=20 V, V_{GS}=0 V, T_j=150 °C	-	-	100	
Gate-source leakage current	I_{GSS}	V_{GS}=12 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=2.5 V, I_D=3 A	-	25	33	mΩ
		V_{GS}=4.5 V, I_D=3.8 A	-	17	21	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=3.8 A		17	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=10 V, f=1 MHz	-	863	1147	pF
Output capacitance	C_{oss}		-	278	370	
Reverse transfer capacitance	C_{rss}		-	40	60	
Turn-on delay time	$t_{d(on)}$	V_{DD}=10 V, V_{GS}=4.5 V, I_D=3.8 A, R_G=6 Ω	-	8.8	-	ns
Rise time	t_r		-	16.7	-	
Turn-off delay time	$t_{d(off)}$		-	19	-	
Fall time	t_f		-	3.7	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=10 V, I_D=3.8 A, V_{GS}=0 to 4.5 V	-	1.66	2.21	nC
Gate to drain charge	Q_{gd}		-	1.1	1.6	
Gate charge total	Q_g		-	5.8	8.8	
Gate plateau voltage	$V_{plateau}$		-	1.9	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	0.8	A
Diode pulse current	$I_{S,pulse}$		-	-	15.2	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=3.8 A, T_j=25 °C	-	0.8	1.1	V
Reverse recovery time	t_{rr}	V_R=10 V, I_F=3.8 A, di_F/dt=100 A/µs	-	14.3		ns
Reverse recovery charge	Q_{rr}		-	7.6	-	nC

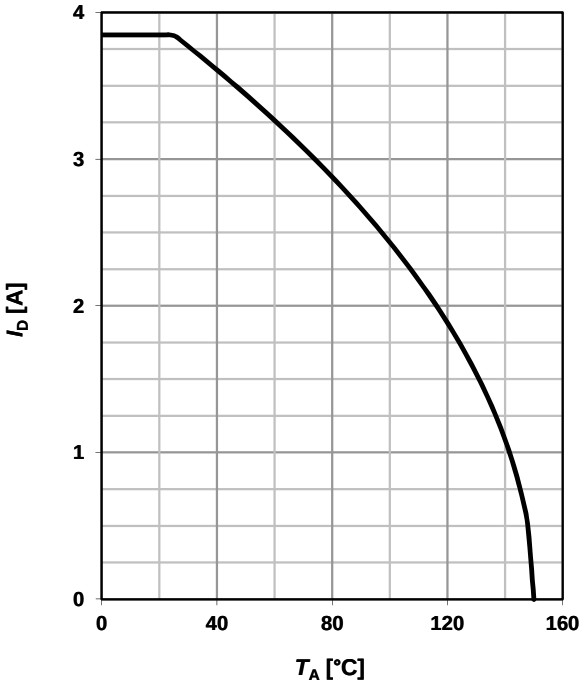
1 Power dissipation

$P_{tot}=f(T_A)$



2 Drain current

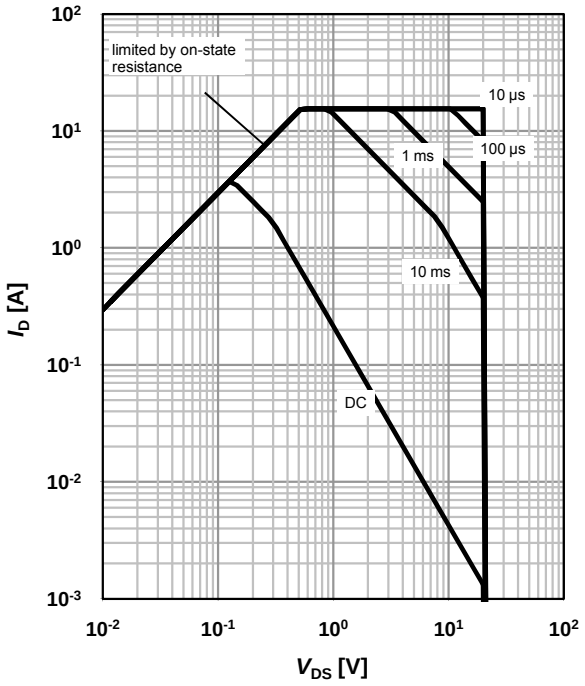
$I_D=f(T_A)$; $V_{GS}\geq 4.5$ V



3 Safe operating area

$I_D=f(V_{DS})$; T_A=25 °C; D=0

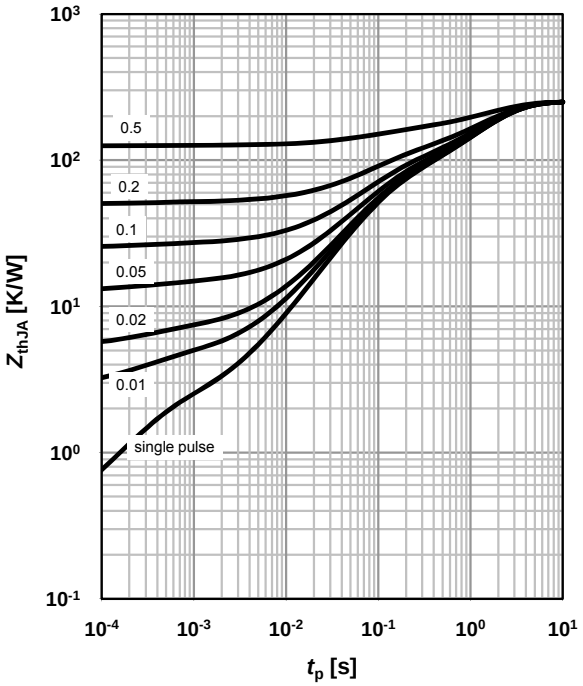
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)$

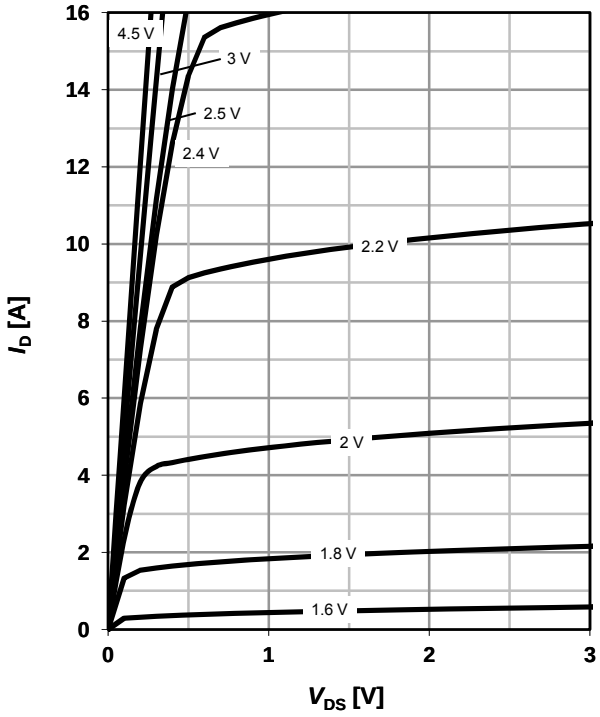
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C

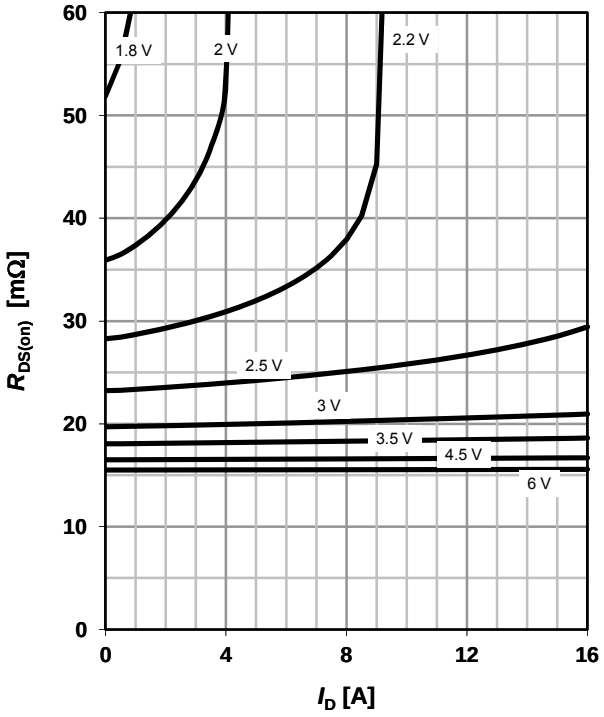
parameter: V_{GS}



6 Typ. drain-source on resistance

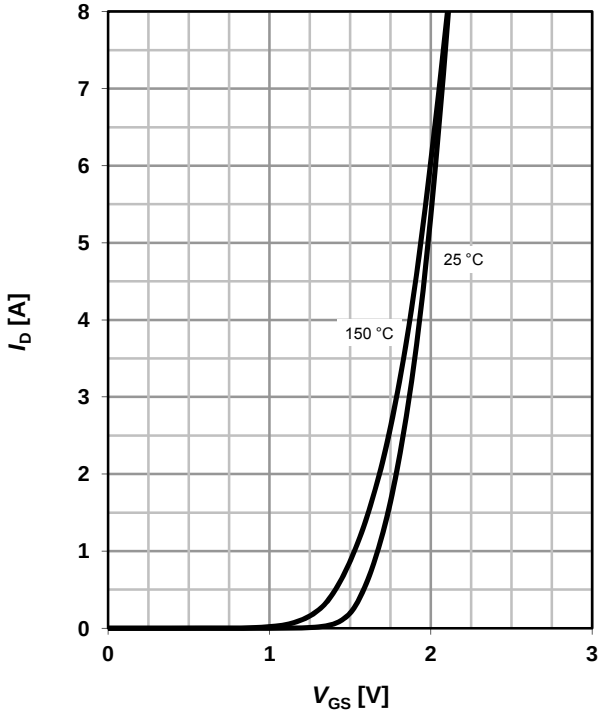
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C

parameter: V_{GS}



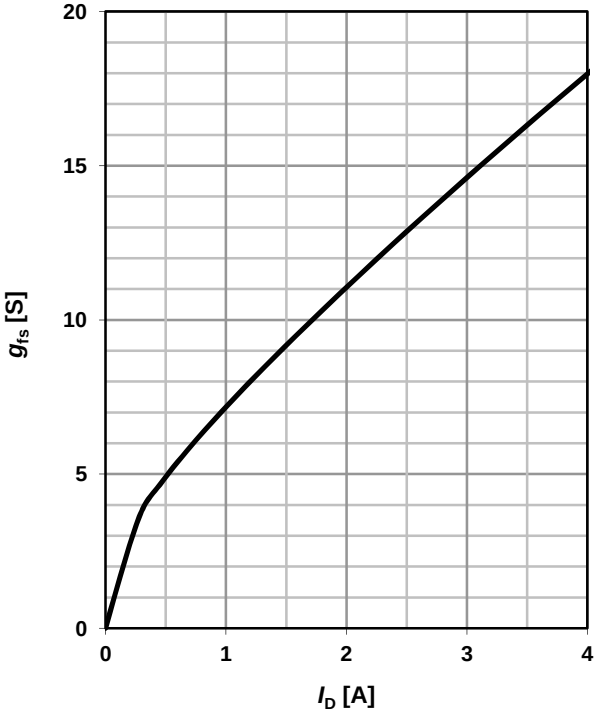
7 Typ. transfer characteristics

$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$



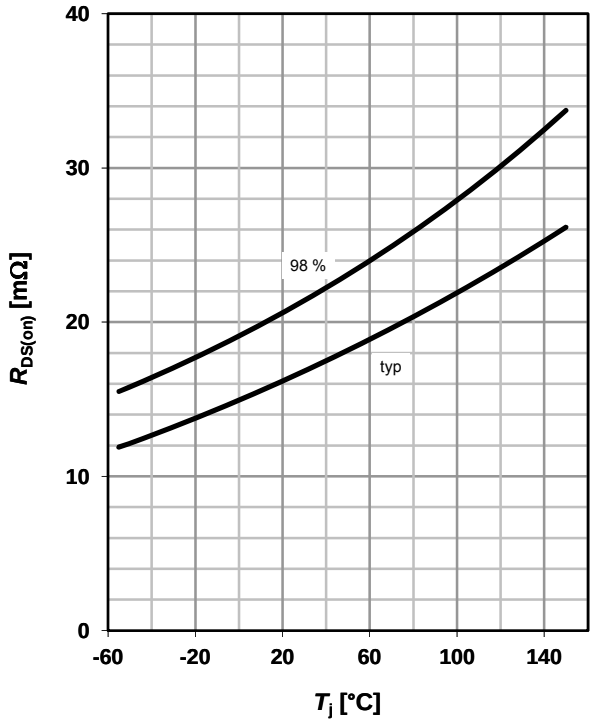
8 Typ. forward transconductance

$g_{fs}=f(I_D)$; $T_j=25$ °C



9 Drain-source on-state resistance

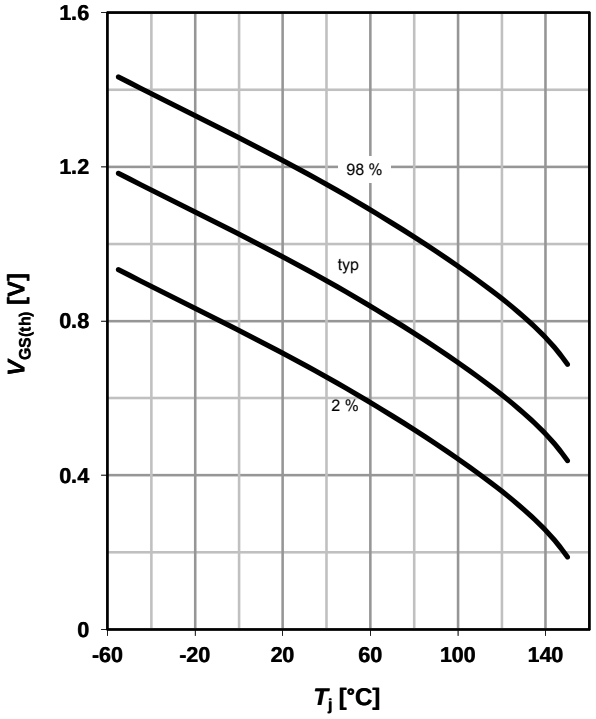
$R_{DS(on)}$=f(T_j); I_D=3.8 A; V_{GS}=4.5 V



10 Typ. gate threshold voltage

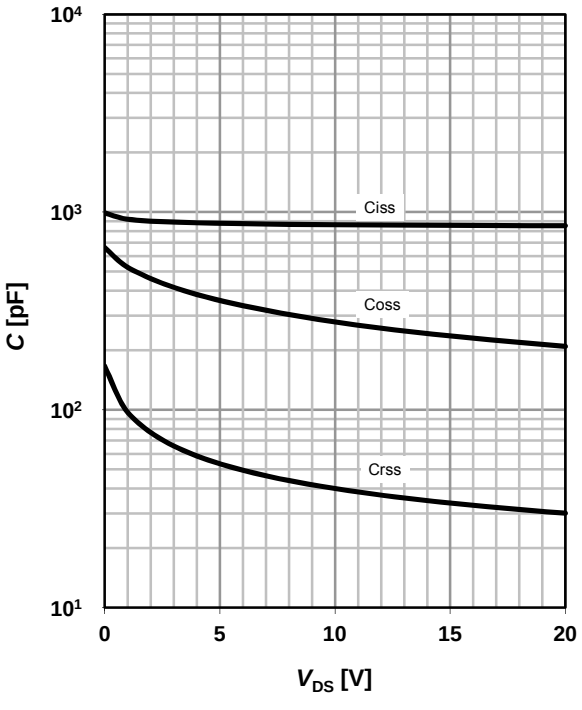
$V_{GS(th)}$=f(T_j); V_{DS}=V_{GS}; I_D=30 µA

parameter: I_D



11 Typ. capacitances

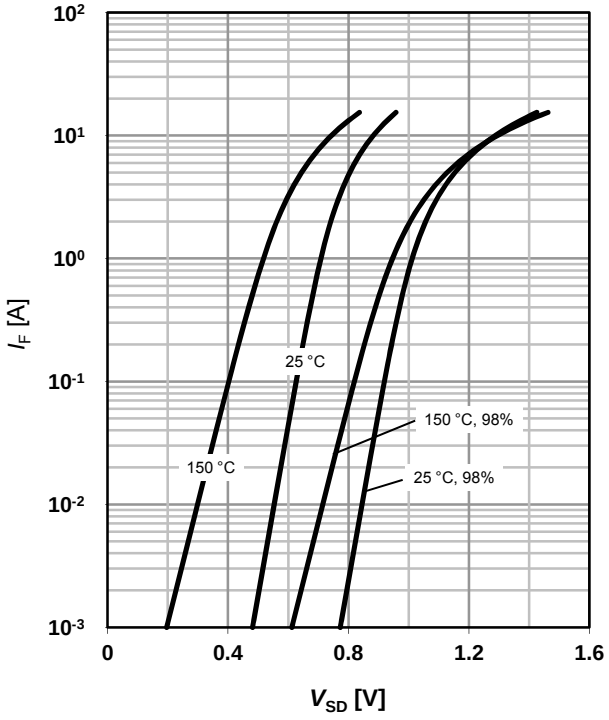
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz; T_j=25°C



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

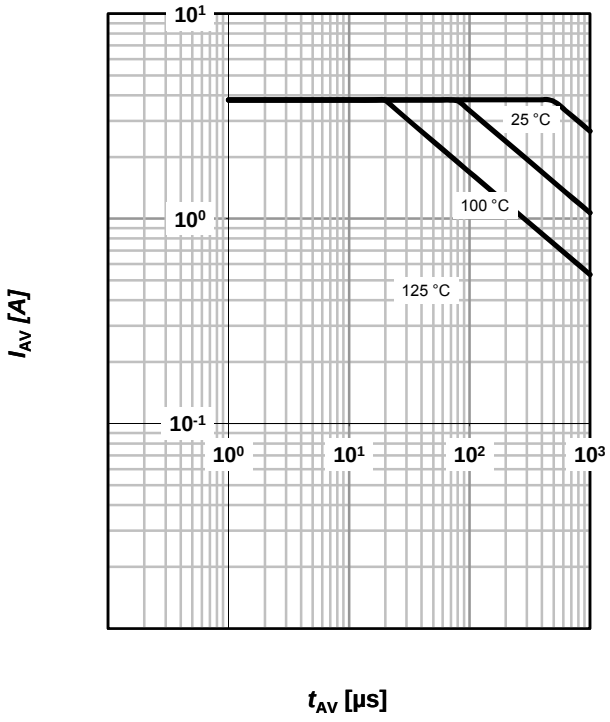
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

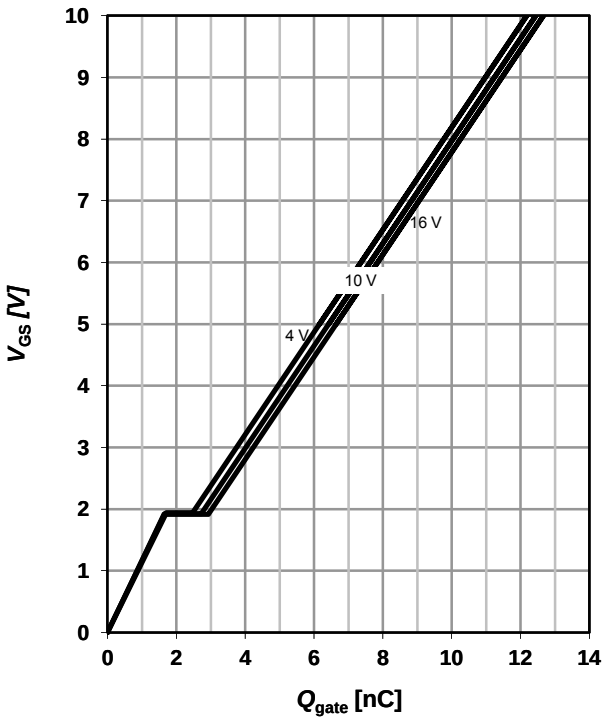
parameter: $T_{j(start)}$



14 Typ. gate charge

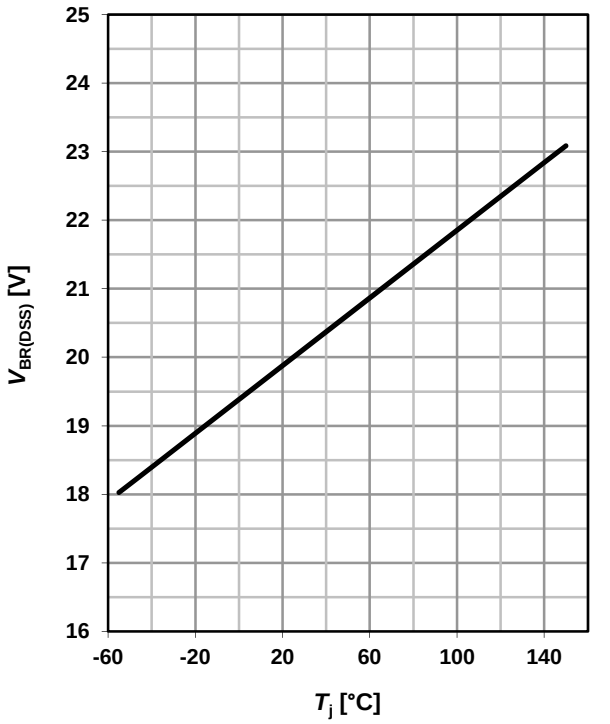
V_{GS}=f(Q_{gate}); I_D=3.8 A pulsed

parameter: V_{DD}

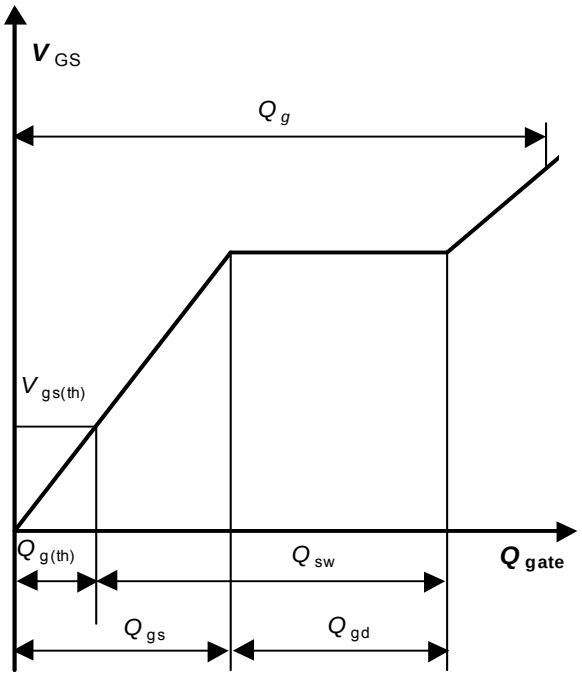


15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=250 µA

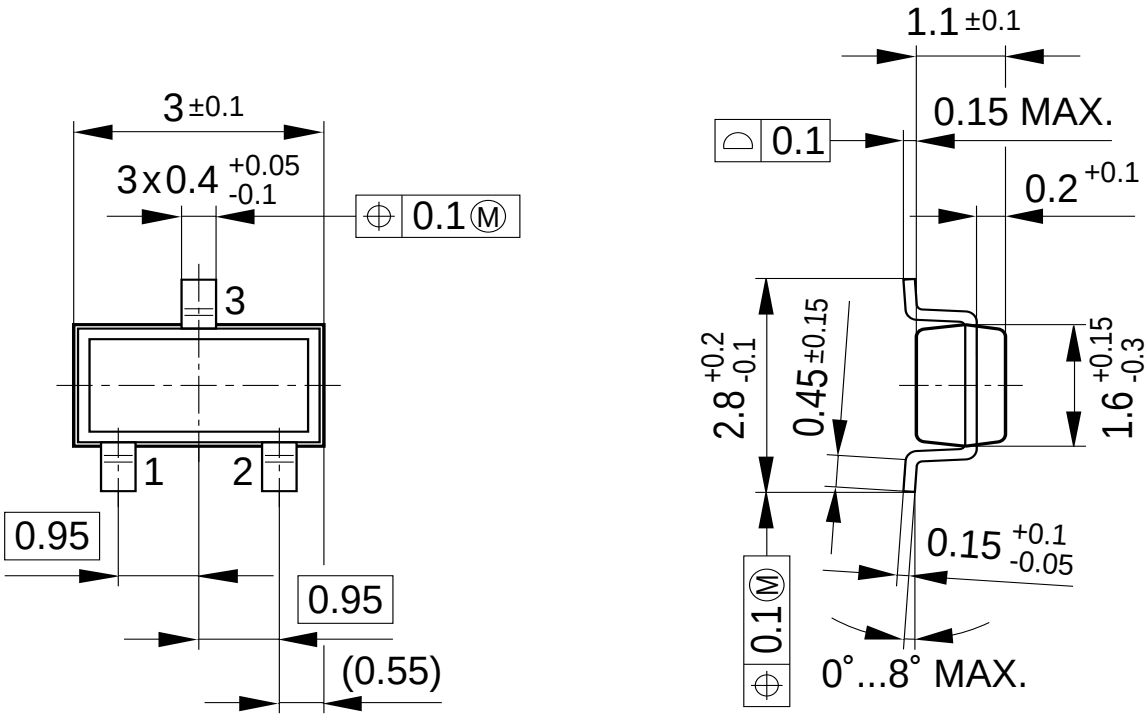


16 Gate charge waveforms



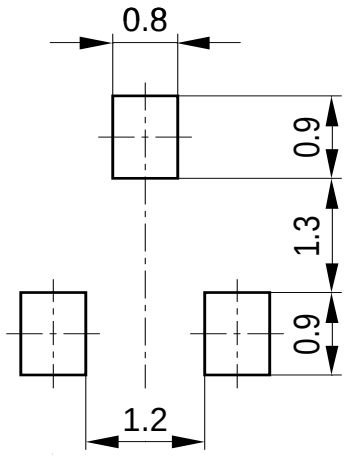
Package Outline:

PG-SC59



GPS09473

Footprint:



HLG09474

Dimensions in mm

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